

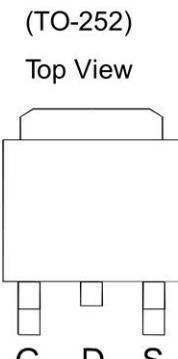
Features

- V_{DS} -100V
- I_D -13A
- R_{DS(ON)} (at V_{GS}=-10V) < 210mΩ

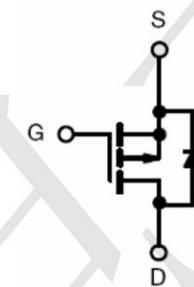
Application

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

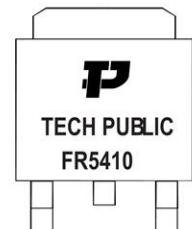
Package and Pin Configuration



1. GATE
2. DRAIN
3. SOURCE



Marking:



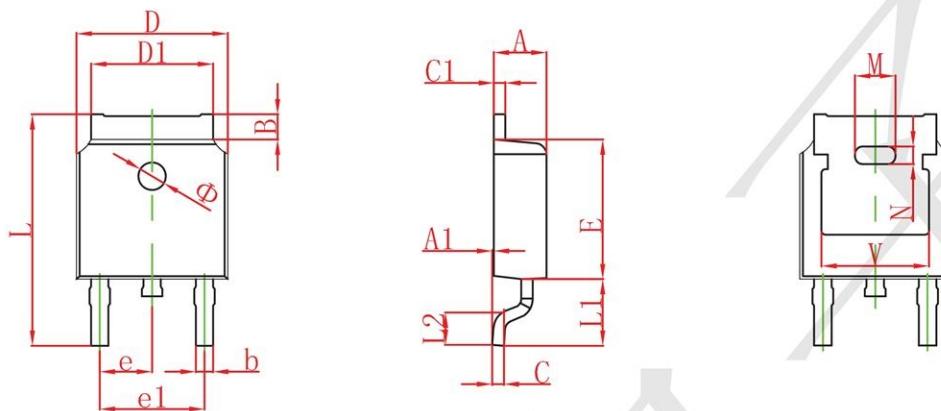
Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	-100	V
Gate-Source Voltage	V _{GS}	±20	
Continuous Drain Current	I _D	-13	A
Pulsed Drain Current ①	I _{DM}	-30	
Continuous Source-Drain Current(Diode Conduction)	I _S	13	
Power Dissipation ②	P _D	66	W
Thermal Resistance from Junction to Ambient (t≤5s)	R _{θJA}	110	°C/W
Operating Junction	T _J	175	°C
Storage Temperature	T _{STG}	-55~+175	°C

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static Parameters						
Drain-Source Breakdown Voltage	BV_{DSS}	$\text{VGS} = 0\text{V}, \text{ID} = -250\mu\text{A}$	-100			V
Gate Threshold Voltage	$\text{V}_{\text{GS(th)}}$	$\text{VDS} = \text{VGS}, \text{ID} = -250\mu\text{A}$	-2		-4	V
Gate-Body leakage Current	I_{GSS}	$\text{VDS} = 0\text{V}, \text{VGS} = \pm 20\text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$\text{VDS} = -100\text{V}, \text{VGS} = 0\text{V}$			-1	μA
Static Drain-Source On-Resistance	$\text{R}_{\text{DS(on)}}$	$\text{VGS} = -10\text{V}, \text{ID} = -6\text{A}$		180	210	$\text{m}\Omega$
Forward Transconductance	g_{fs}	$\text{VDS} = -50\text{V}, \text{ID} = -12\text{A}$		3.2		S
Diode Forward Voltage	V_{SD}	$\text{IS} = -1\text{A}, \text{VGS} = 0\text{V}$		-0.8	-1.2	V
Dynamic Parameters						
Input Capacitance	C_{iss}	$\text{VDS} = -30\text{V}, \text{VGS} = 0\text{V}, \text{f} = 1\text{MHz}$		760		pF
Output Capacitance	C_{oss}			260		pF
Reverse Transfer Capacitance	C_{rss}			170		pF
Total Gate Charge	Q_{g}	$\text{VDS} = -80\text{V}, \text{VGS} = -10\text{V}, \text{ID} = -12\text{A}$		58		nC
Gate Source Charge	Q_{gs}			8.3		nC
Gate Drain Charge	Q_{gd}			32		nC
Switching Parameters						
Turn-On DelayTime	td(on)	$\text{VDD} = -50\text{V}$ $\text{RL} = 10\Omega, \text{ID} = -8.4\text{A}$, $\text{VGEN} = -10\text{V}, \text{R}_g = 9\Omega$		130		ns
Turn-On Rise Time	tr			130		ns
Turn-Off DelayTime	td(off)			135		ns
Turn-Off Fall Time	tf			140		ns

TO252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.380	0.087	0.094
A1	0.000	0.100	0.000	0.004
B	0.800	1.400	0.031	0.055
b	0.710	0.810	0.028	0.032
c	0.460	0.560	0.018	0.022
c1	0.460	0.560	0.018	0.022
D	6.500	6.700	0.256	0.264
D1	5.130	5.460	0.202	0.215
E	6.000	6.200	0.236	0.244
e	2.286 TYP.		0.090 TYP.	
e1	4.327	4.727	0.170	0.186
M	1.778REF.		0.070REF.	
N	0.762REF.		0.018REF.	
L	9.800	10.400	0.386	0.409
L1	2.9REF.		0.114REF.	
L2	1.400	1.700	0.055	0.067
V	4.830 REF.		0.190 REF.	
Φ	1.100	1.300	0.043	0.051